

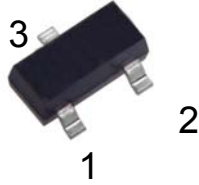
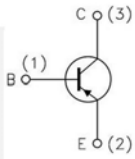


SOT-23 Plastic-Encapsulate Transistors

 <p>MMBT5401</p> <p>Features:</p> <ul style="list-style-type: none"> <input type="checkbox"/> PNP Transistor <input type="checkbox"/> Complementary to MMBT5551 <input type="checkbox"/> Ideal for Medium Power Amplification and Switching <p>Marking:2L</p>	<p>SOT-23</p>    <p>1.Base (B) 2. Emitter (E) 3. Collector (C)</p>
---	---

Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-160	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	0.6	A
Collector Power Dissipation	PD	0.3	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	416	°C/W
Junction Temperature(MAX.)	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics (Ta=25°C unless otherwise noted)

Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-160	-	-	V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-150	-	-	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5	-	-	V
Collector cut-off current	I_{CBO}	$V_{CB}=-120V, I_E=0$	-	-	-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$	-	-	-0.1	μA
DC current gain	$h_{FE(1)}$ *	$V_{CE}=-5V, I_C=-1mA$	80	-	-	-
	$h_{FE(2)}$ *	$V_{CE}=-5V, I_C=-10mA$	100	-	300	-
	$h_{FE(3)}$ *	$V_{CE}=-5V, I_C=-50mA$	50	-	-	-
Collector-emitter saturation voltage	$V_{CE(sat)1}$ *	$I_C=-10mA, I_B=-1mA$	-	-	-0.2	V
	$V_{CE(sat)2}$ *	$I_C=-50mA, I_B=-5mA$	-	-	-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)1}$ *	$I_C=-10mA, I_B=-1mA$	-	-	-1	V
	$V_{BE(sat)2}$ *	$I_C=-50mA, I_B=-5mA$	-	-	-1	V
Transition frequency	FT	$V_{CE}=-5V, I_C=-10mA, f=30MHz$	100	-	-	MHz

CLASSIFICATION OF hFE (2)

RANK	L	H
RANGE	100-200	200-300

*Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2.0\%$.

SOT-23 Plastic-Encapsulate Transistors

Typical Characteristics

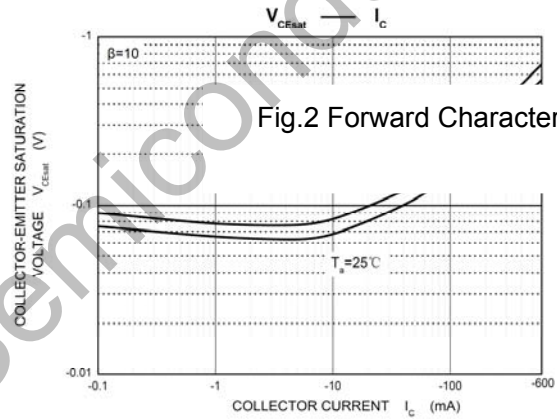
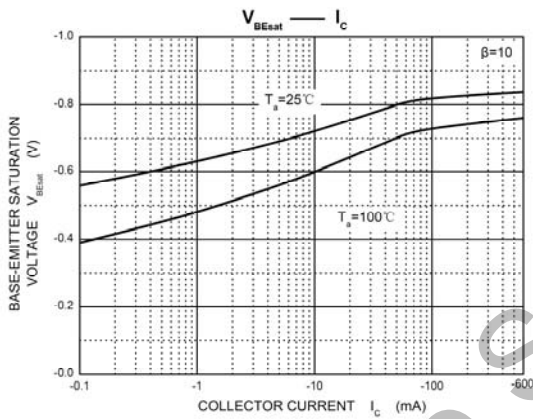
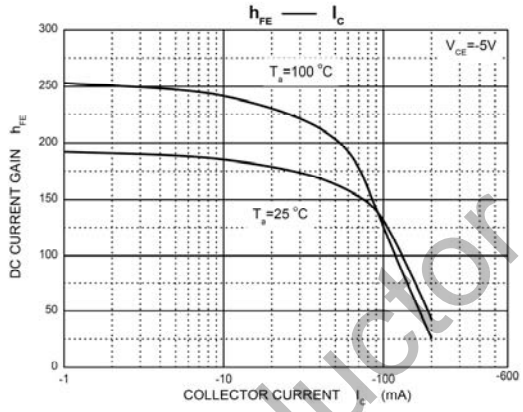
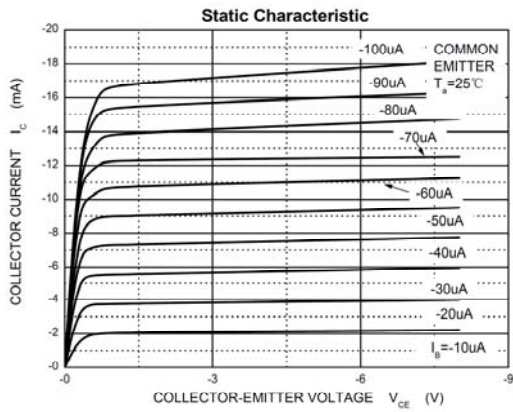
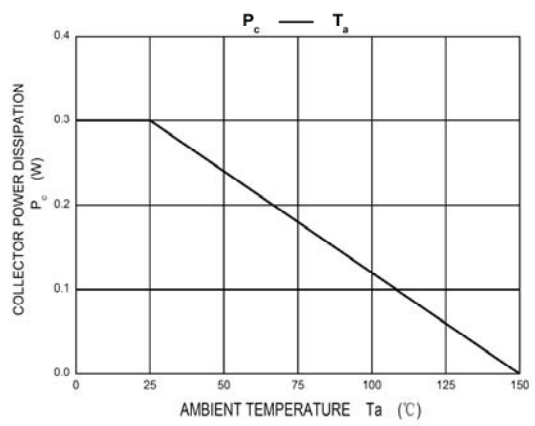
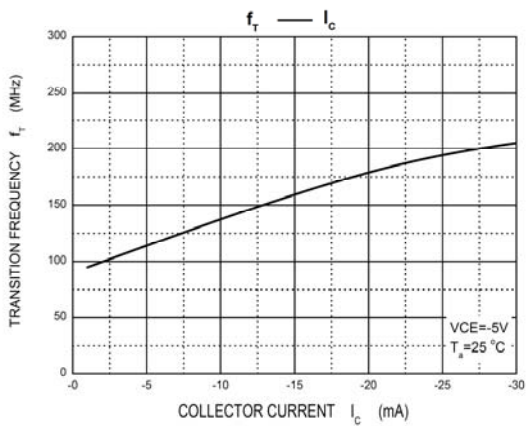
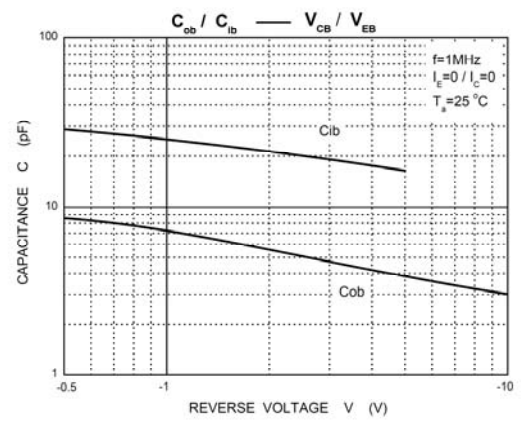
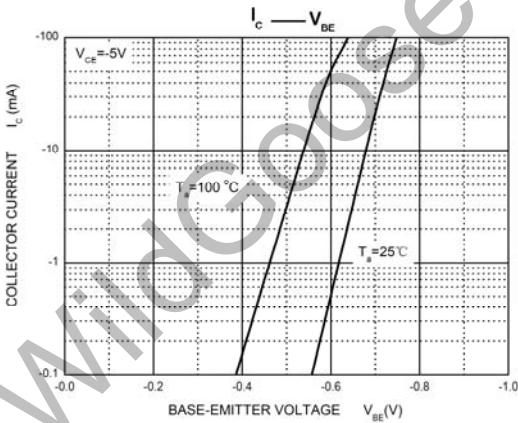


Fig.2 Forward Characteristics

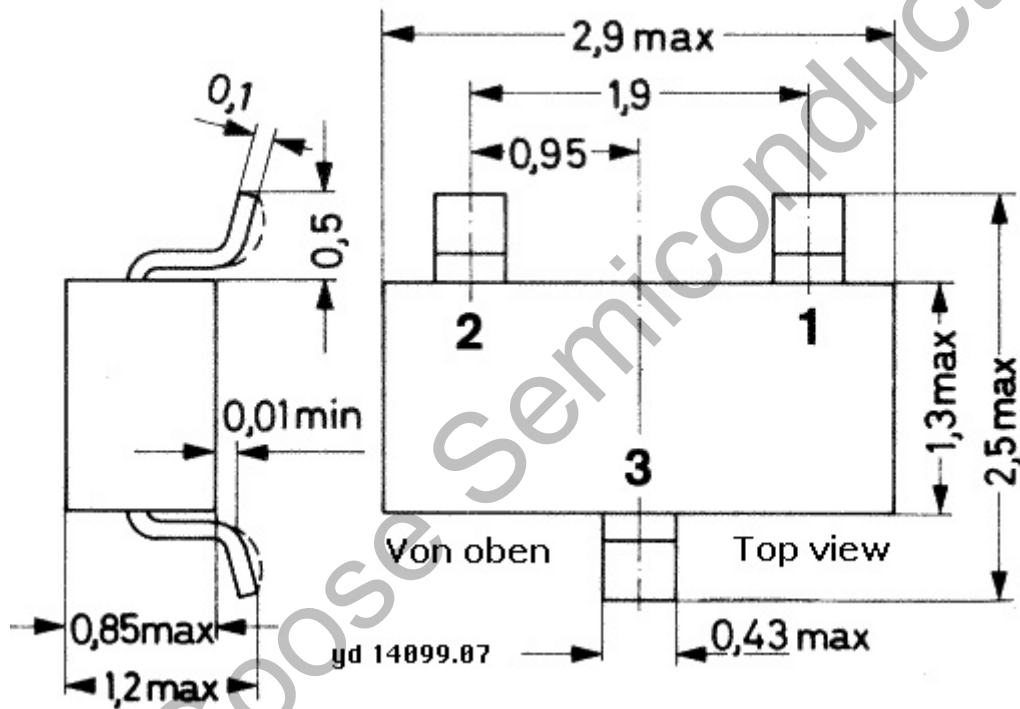


SOT-23 Plastic-Encapsulate Transistors

Package Dimension

SOT-23

Unit: mm



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - BJT category](#):

Click to view products by [Wild Goose manufacturer](#):

Other Similar products are found below :

[BC559C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [NJVMJD148T4G](#) [NTE16](#) [NTE195A](#) [IMX9T110](#) [2N4401-A](#) [2N6728](#) [2SA1419T-TD-H](#) [2SB1204S-TL-E](#) [2SC5488A-TL-H](#) [FMC5AT148](#) [2N2369ADCSM](#) [2N2907A](#) [2N3904-NS](#) [2N5769](#) [2SC4618TLN](#) [CPH6501-TL-E](#) [BC856BW-13-F](#) [US6T6TR](#) [BAX18/A52R](#) [BC556/112](#) [IMZ2AT108](#) [MMST8098T146](#) [MCH6102-TL-E](#) [BC846B-13-F](#) [2N3879](#) [30A02MH-TL-E](#) [NTE13](#) [NTE282](#) [NTE323](#) [NTE350](#) [NTE81](#) [JANTX2N2920L](#) [JANSR2N2907AUB](#) [CMLT3946EG TR](#) [SNSS40600CF8T1G](#) [CMLT3906EG TR](#) [GRP-DATA-JANS2N2907AUB](#) [GRP-DATA-JANS2N2222AUA](#) [MMDT3946FL3-7](#) [2N4240](#) [JANS2N3019](#) [MSB30KH-13](#) [2N2221AUB](#) [2SD1815T-TL-E](#) [2N6678](#) [2N2907Ae4](#)